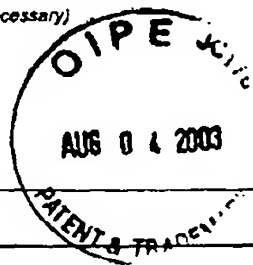


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 First Named Inventor Ahn, Kie  
 Group Art Unit 2814  
 Examiner Name Pham, Long

Sheet 1 of 6

Attorney Docket No: 1303.030US1

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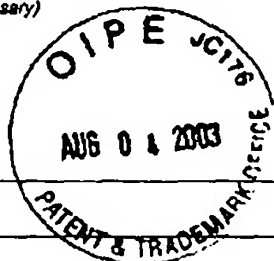
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Sheet 2 of 6

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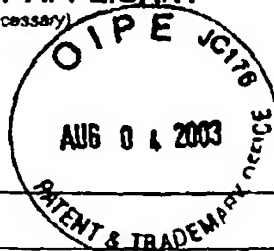
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First Named Inventor	Ahn, Kie
Group Art Unit	2814
Examiner Name	Pham, Long

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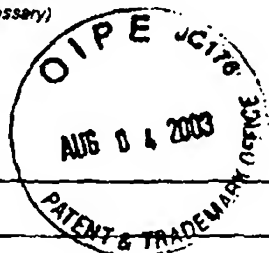
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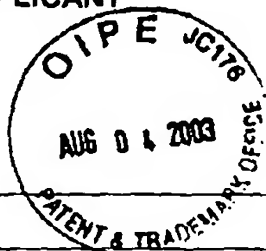
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